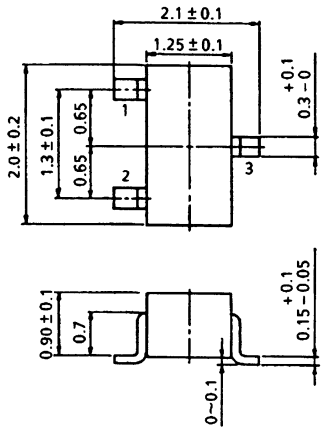
TOSHIBA SemiconductorTOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK880

Audio Frequency Low Noise Amplifier Applications

- High $|Y_{fs}|$: $|Y_{fs}|$ = 15 mS (typ.) at V_{DS} = 10 V, V_{GS} = 0
- High breakdown voltage: V_{GDS} = −50 V
- Low noise: NF = 1.0dB (typ.)
  at V_{DS} = 10 V, I_D = 0.5 mA, f = 1 kHz, R_G = 1 kΩ
- High input impedance: I_{GSS} = −1 nA (max) at V_{GS} = −30 V
- Small package

Unit: mm



1. SOURCE
2. DRAIN
3. GATE

USM

JEDEC	—
JEITA	SC-70
TOSHIBA	2-2E1B

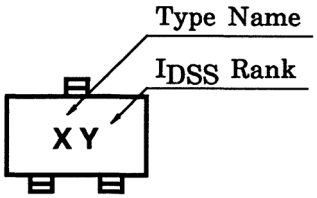
Weight: 0.006 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDS}	−50	V
Gate current	I_G	10	mA
Drain power dissipation	P_D	100	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking

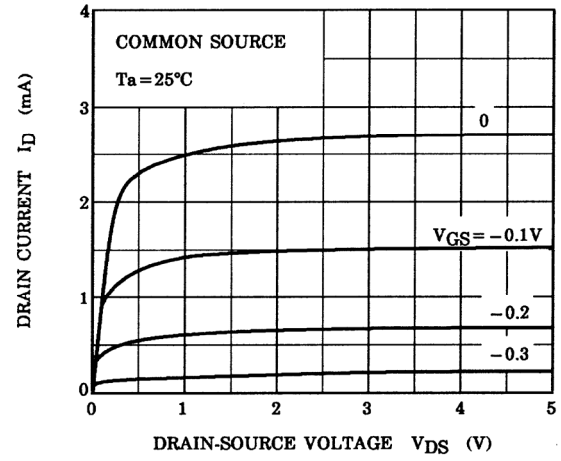


Electrical Characteristics (Ta = 25°C)

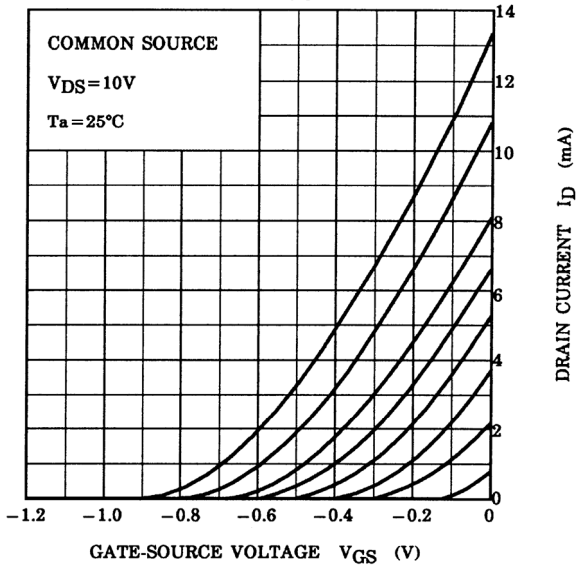
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate cut-off current	I_{GSS}	V_{GS} = −30 V, V_{DS} = 0	—	—	−1.0	nA
Gate-drain breakdown voltage	$V_{(BR)\ GDS}$	V_{DS} = 0, I_G = −100 μA	−50	—	—	V
Drain current	I_{DSS} (Note)	V_{DS} = 10 V, V_{GS} = 0	1.2	—	14.0	mA
Gate-source cut-off voltage	$V_{GS\ (OFF)}$	V_{DS} = 10 V, I_D = 0.1 μA	−0.2	—	−1.5	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS} = 10 V, V_{GS} = 0, f = 1 kHz	4.0	15	—	mS
Input capacitance	C_{iss}	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz	—	13	—	pF
Reverse transfer capacitance	C_{rss}	V_{DG} = 10 V, I_D = 0, f = 1 MHz	—	3	—	pF
Noise figure	NF (1)	V_{DS} = 10 V, R_G = 1 kΩ I_D = 0.5 mA, f = 10 Hz	—	5	—	dB
	NF (2)	V_{DS} = 10 V, R_G = 1 kΩ I_D = 0.5 mA, f = 1 kHz	—	1	—	

Note: I_{DSS} classification Y: 1.2~3.0 mA, GR: 2.6~6.5 mA, BL: 6.0~14 mA

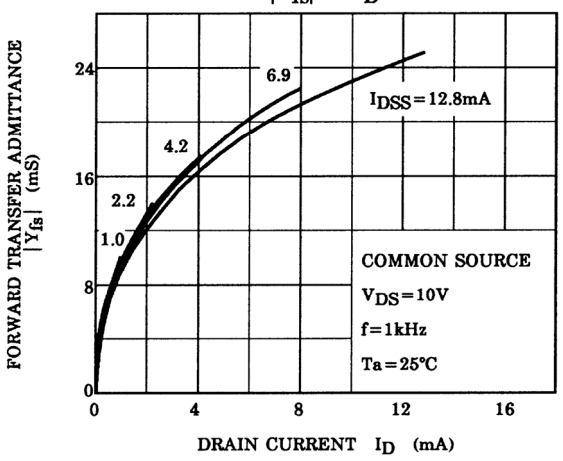
$I_D - V_{DS}$



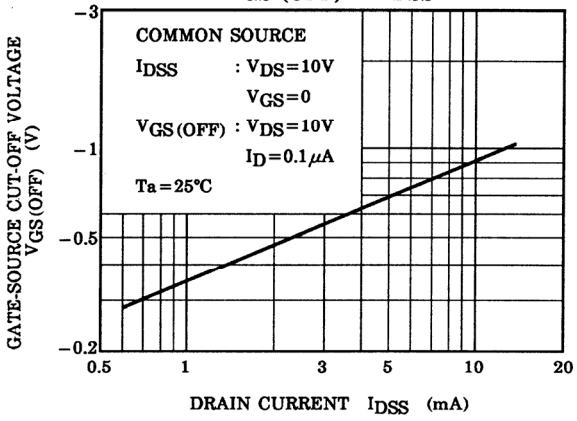
$I_D - V_{GS}$



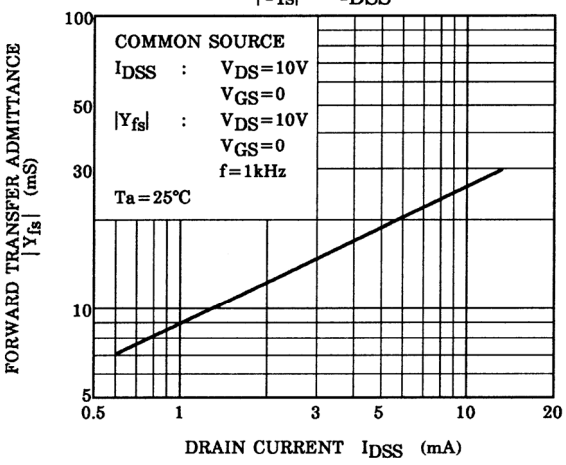
$|Y_{fs}| - I_D$



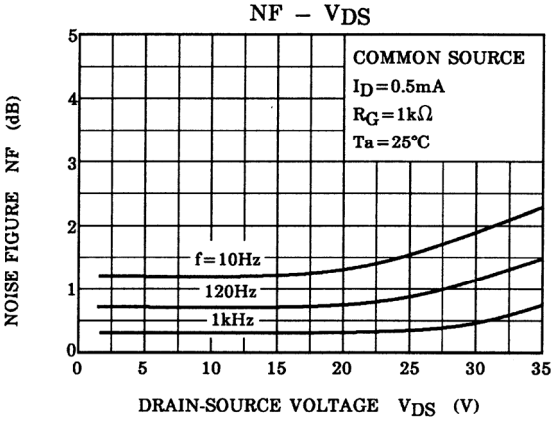
$V_{GS\ (OFF)} - I_{DSS}$



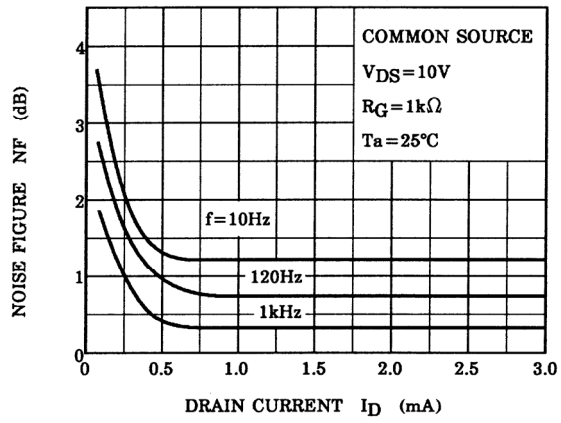
$|Y_{fs}| - I_{DSS}$



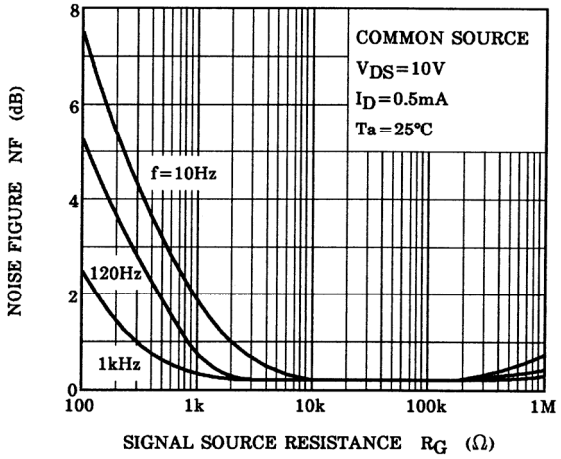
NF − V_{DS}



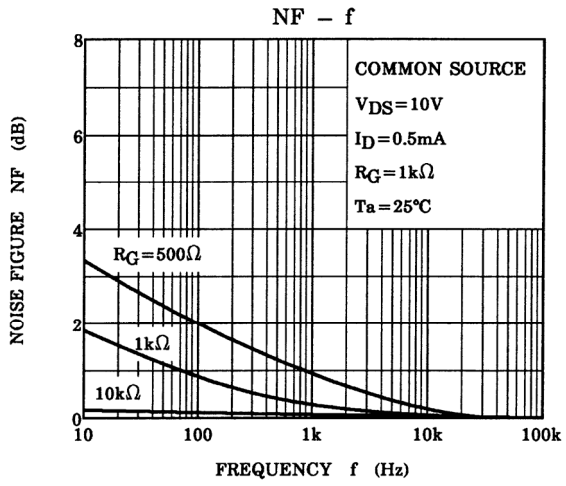
NF – I_D



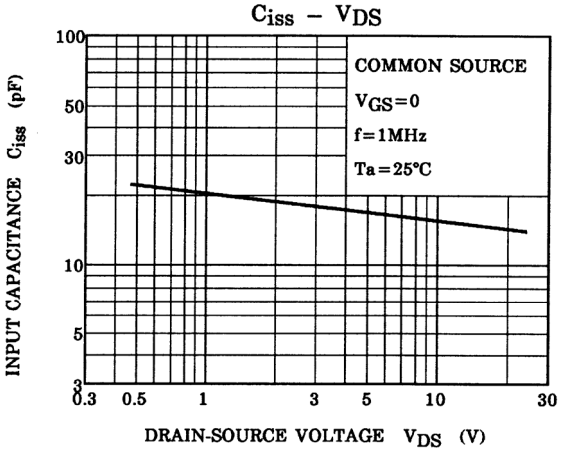
NF – R_G



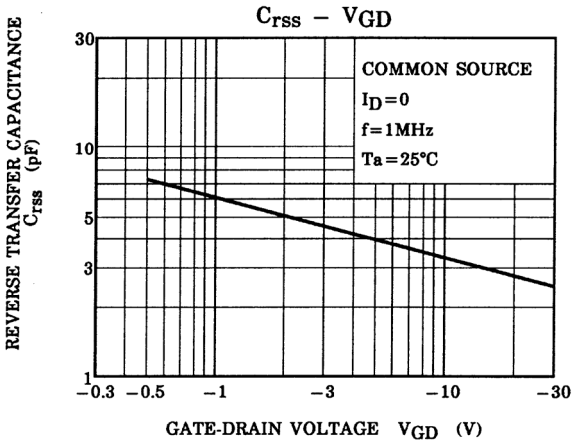
NF – f



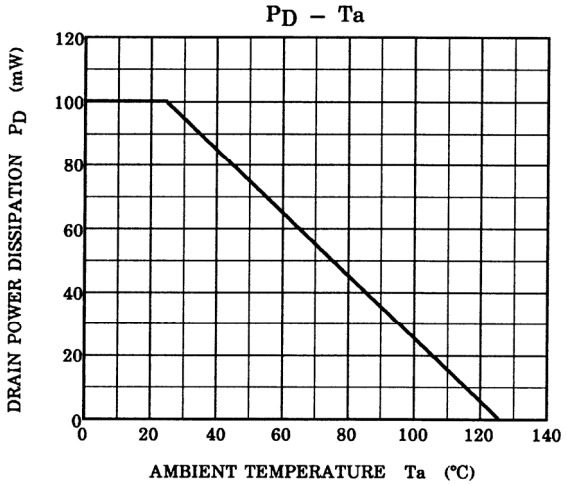
C_{iss} – V_{DS}



C_{rss} – V_{GD}



P_D – Ta



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20070701-EN GENERAL

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